

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	("6501149").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 13:48
S2	791	"257".clas. and Idmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:03
S3	791	"257".clas. and Idmos and ap<"20040409"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:03
S4	748	"257".clas. and Idmos and @ad<"20040409"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:03
S5	254	"257".clas. and Idmos and @ad<"20040409" and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:05
S6	53	"257".clas. and Idmos and @ad<"20040409" and trench and leakage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:51
S7	65	"257".clas. and Idmos and @ad<"20040409" and (trench or STI or LOCOS) and leakage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 15:36
S8	492	(257/499).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 13:48

S9	120	257/499.ccls. and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 13:54
S10	114	257/499.ccls. and trench and @ad<"20040409"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:46
S11	609	257/510.ccls. and trench and @ad<"20040409"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:46
S12	486	257/510.ccls. and trench and @ad<"20040409" and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:47
S13	218	257/510.ccls. and trench and @ad<"20040409" and transistor and leakage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:47
S14	63	257/510.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:27
S15	9	257/511.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:32
S16	1	257/512.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:33

S17	24	257/513.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:39
S18	11	257/514.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:45
S19	7	257/515.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:46
S20	3	257/547.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:49
S21	17	257/335.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 15:59
S22	158	438/424.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 12:45
S23	256	trench and @ad<"20040409" and ("corner vt") or ("corner transistor") or ("gate edge drain leakage") or ("corner leakage") or ("edge conduction") or ("sidewall leakage") or ("side wall leakage") or ("side-wall leakage") or ("edge leakage"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 14:01
S24	253	257/408.ccls. and trench and @ad<"20040409"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 14:01

S25	241	257/408.ccls. and trench and @ad<"20040409" and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 14:02
S26	48	257/506.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 16:27
S27	3	257/213.ccls. and trench and @ad<"20040409" and (transistor with leakage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 13:25
S28	89	trench and @ad<"20040409" and (transistor with leakage) and (strained or SMOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:31
S29	97	trench and @ad<"20040409" and (transistor with leakage) and ("body contact")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/10 16:31